

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

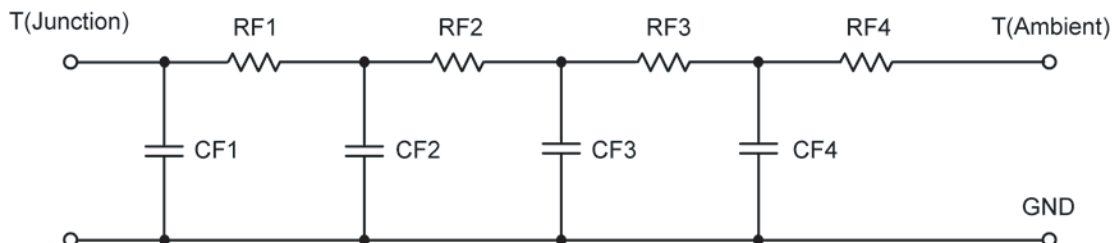
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	20.6695	N/A	6.7820
RT2	2.1357	N/A	533.7090 m
RT3	23.4290	N/A	7.5334
RT4	33.4871	N/A	4.1491
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	25.0230 m	N/A	71.2795 m
CT2	1.7123 m	N/A	903.0670 u
CT3	358.8393 m	N/A	10.2637 m
CT4	1.9282	N/A	739.5354 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	8.8432	N/A	3.8300
RF2	20.5851	N/A	8.8945
RF3	25.7815	N/A	4.8422
RF4	24.4480	N/A	1.3472
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	8.1411 m	N/A	5.0276 m
CF2	31.5787 m	N/A	9.4290 m
CF3	346.1198 m	N/A	247.8448 m
CF4	2.0902	N/A	800.0707 u

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

